

Tong Wu

List of Publications by Year in descending order

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Version: 2024-02-01

14
papers

107
citations

1478505

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1372567

10
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all docs

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times ranked

154
citing authors

#	ARTICLE	IF	CITATIONS
1	Tunneling current in HfO ₂ and Hf _{0.5} Zr _{0.5} O ₂ -based ferroelectric tunnel junction. Journal of Applied Physics, 2018, 123, .	2.5	27
2	Speed Up Quantum Transport Device Simulation on Ferroelectric Tunnel Junction With Machine Learning Methods. IEEE Transactions on Electron Devices, 2020, 67, 5229-5235.	3.0	15
3	A Tantalum Disulfide Charge-Density-Wave Stochastic Artificial Neuron for Emulating Neural Statistical Properties. Nano Letters, 2021, 21, 3465-3472.	9.1	15
4	Reconfigurable Stochastic neurons based on tin oxide/MoS ₂ hetero-memristors for simulated annealing and the Boltzmann machine. Nature Communications, 2021, 12, 5710.	12.8	14
5	Multiobjective Design of 2-D-Material-Based Field-Effect Transistors With Machine Learning Methods. IEEE Transactions on Electron Devices, 2021, 68, 5476-5482.	3.0	6
6	Multiscale modeling of semimetal contact to two-dimensional transition metal dichalcogenide semiconductor. Applied Physics Letters, 2022, 121, .	3.3	6
7	Performance Potential of 2D Kagome Lattice Interconnects. IEEE Electron Device Letters, 2019, 40, 1973-1975.	3.9	5
8	Compact Model of Carrier Transport in Monolayer Transition Metal Dichalcogenide Transistors. IEEE Transactions on Electron Devices, 2019, 66, 177-183.	3.0	4
9	Variability and Fidelity Limits of Silicon Quantum Gates Due to Random Interface Charge Traps. IEEE Electron Device Letters, 2020, , 1-1.	3.9	4
10	Computational Assessment of Silicon Quantum Gate Based on Detuning Mechanism for Quantum Computing. IEEE Transactions on Electron Devices, 2018, 65, 5530-5536.	3.0	3
11	Performance Assessment of Resonantly Driven Silicon Two-Qubit Quantum Gate. IEEE Electron Device Letters, 2018, 39, 1096-1099.	3.9	3
12	A Multiscale Simulation Approach for Germanium-Hole-Based Quantum Processor. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2023, 42, 257-265.	2.7	3
13	A computational study of spin Hall effect device based on 2D materials. Journal of Applied Physics, 2020, 128, 014303.	2.5	1
14	Electroluminescence of atoms in a graphene nanogap. Science Advances, 2022, 8, eabj1742.	10.3	1